

Bibliography

- [1] G. ALI, D. BINI AND S. RIONERO, Global existence and relaxation limit for smooth solutions to the Euler-Poisson model for semiconductors, *SIAM J. Math. Anal.* **32** (2000), 572–587.
- [2] N. BEN ABDALLAH, P. DEGOND AND S. GENIEYS, An energy-transport model for semiconductors derived from the Boltzmann equation, *J. Statist. Phys.* **84** (1996), 205–231.
- [3] N. BEN ABDALLAH, P. DEGOND AND S. GENIEYS, On a hierarchy of macroscopic models for semiconductor, *J. Math. Phys.* **37** (1996), 3306–3333.
- [4] K. BLØTEKJÆR, Transport equations for electrons in two-valley semiconductors, *IEEE Trans. Electron Devices* **17** (1970), 38–47.
- [5] L. CHEN, L. HSIAO AND Y. LI, Large time behavior and energy relaxation time limit of the solutions to an energy transport model in semiconductors, *J. Math. Anal. Appl.* **312** (2005), 596–619.
- [6] G. Q. CHEN, J. W. JEROME AND B. ZHANG, Particle hydrodynamic moment models in biology and microelectronics: Singular relaxation limits , *Nonlinear Analysis* **30** (1997), 233–244.
- [7] P. DEGOND, S. GENIEYS AND A. JUNGEL, A system of parabolic equations in nonequilibrium thermodynamics including thermal and electrical effects, *J. Math. Pures Appl.* **76** (1997), 991–1015.
- [8] P. DEGOND, S. GENIEYS AND A. JUNGEL, A steady-state system in nonequilibrium thermodynamics including thermal and electrical effects, *Math. Methods Appl. Sci.* **21** (1998), 1399–1413.
- [9] P. DEGOND AND P. MARKOWICH, On a one-dimensional steady-state hydrodynamic model, *Appl. Math. Lett.* **3** (1990), 25–29.
- [10] C. L. GARDNER, The quantum hydrodynamic model for semiconductor devices, *SIAM J. Appl. Math.* **54** (1994), 409–427.
- [11] H. GAJEWSKI AND K. GROGER, On the basic equations for carrier transport in semiconductors. *J. Math. Anal. Appl.* **113** (1986), 12–35.
- [12] D. GILBARG AND N. S. TRUDINGER, Elliptic partial differential equations of second order, *Springer-Verlag* 1983.
- [13] T. GRASSER, T. W. TANG, H. KOSINA AND S. SELBERHERR, A Review of Hydrodynamic and Energy-Transport Models for Semiconductor Device Simulation *Proceedings of the IEEE* **91** (2003), 251–274.